

Features :

- Isolated mounting base 2500V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- Inverter
- Inductive heating
- Chopper

V_{RSM}	V_{RRM}	Type
900V	800V	Mx150DF80
1100V	1000V	Mx150DF100
1300V	1200V	Mx150DF120
1500V	1400V	Mx150DF140
1700V	1600V	Mx150DF160
1900V	1800V	Mx150DF180

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}C)$	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, $T_c=100^{\circ}C$	150			150	A
$I_{F(RMS)}$	RMS forward current					236	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			40	mA
I_{FSM}	Surge forward current	10ms half sine wave $V_R=0.6V_{RRM}$	150			3.80	kA
I^2t	I^2t for fusing coordination					72	$A^2s \cdot 10^3$
V_{FO}	Threshold voltage		150			1.05	V
r_F	Forward slope resistance					1.00	mΩ
V_{FM}	Peak forward voltage	$I_{FM}=450A$	25			1.65	V
t_{rr}	Reverse recovery time	$I_{FM}=200A, t_p=2000\mu s,$ $-di/dt=20A/\mu s, V_R=50V$	150			4.0	μs
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.220	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.040	$^{\circ}C/W$
F_m	Terminal connection torque(M8)				12.0		N·m
	Mounting torque(M6)				6.0		N·m
V_{iso}	Isolation voltage	50Hz, R.M.S, $t=1min, I_{iso}: 1mA(MAX)$		2500			V
T_{vj}	Junction temperature			-40		140	$^{\circ}C$
T_{stg}	Stored temperature			-40		125	$^{\circ}C$
W_t	Weight				810		g
Outline	M03						

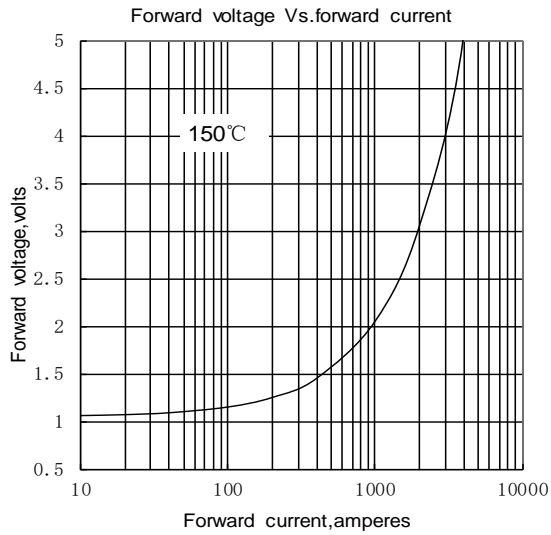


Fig.1

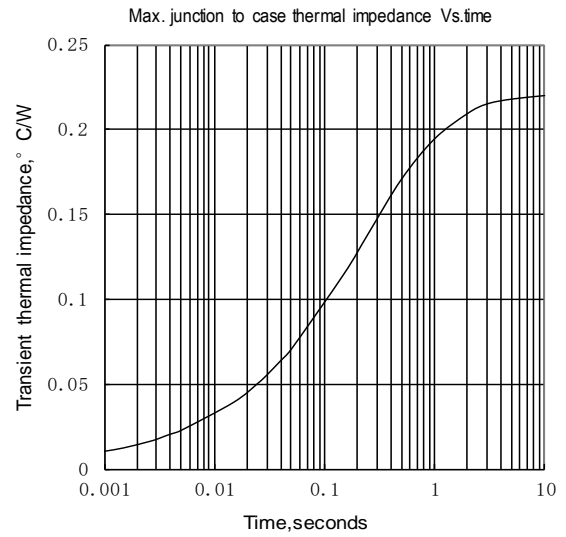


Fig.2

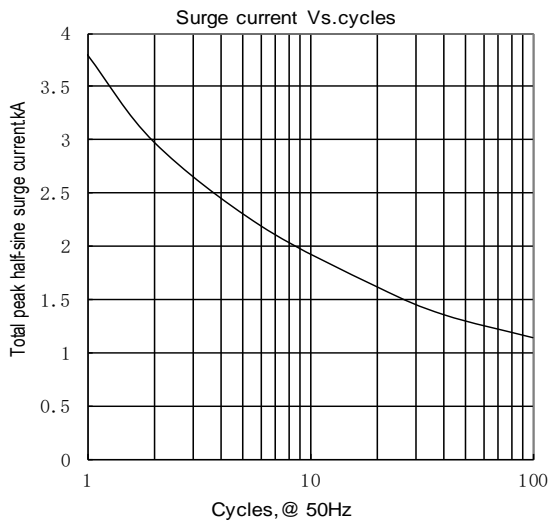


Fig.3

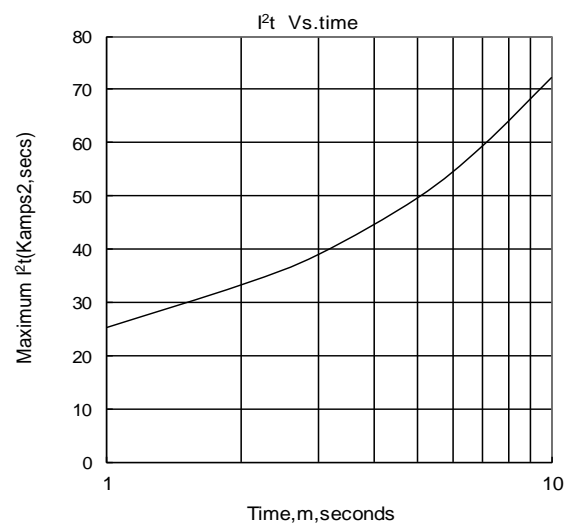


Fig.4

Outline:

